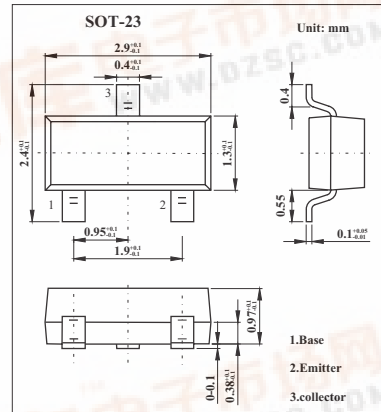


SMD Type Transistors

Silicon NPN Epitaxial
2SC3121

■ Features

- High Transition Frequency :fT=1500MHz (Typ.)
- Exellent Linearity



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	30	V
Collector-emitter voltage	V _{CEO}	15	V
Emitter-base voltage	V _{EB0}	3	V
Collector current	I _c	25	mA
Base current	I _B	50	mA
Collector Power Dissipation	P _c	150	mW
Junction temperature	T _j	125	°C
Storage temperature Range	T _{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	I _{CB0}	V _{CB} = 15V, I _E = 0			0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = 3V, I _c = 0			1.0	μA
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c =1mA, I _B =0	15			V
DC current gain	h _{FE}	V _{CE} = 3 V, I _c = 8 mA	60	150	320	
Transition Frequency	f _T	V _{CE} = 10 V, I _c = 8mA	1100	1500		MHz
Conversion Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0mA, f=1MHZ		0.9	1.3	pF
Collector-Bace Time Constant	C _{c.rbb2}	V _{CB} =10V, I _c =8mA, f=30MHZ		7	12	ps

■ Marking

Marking	HC
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